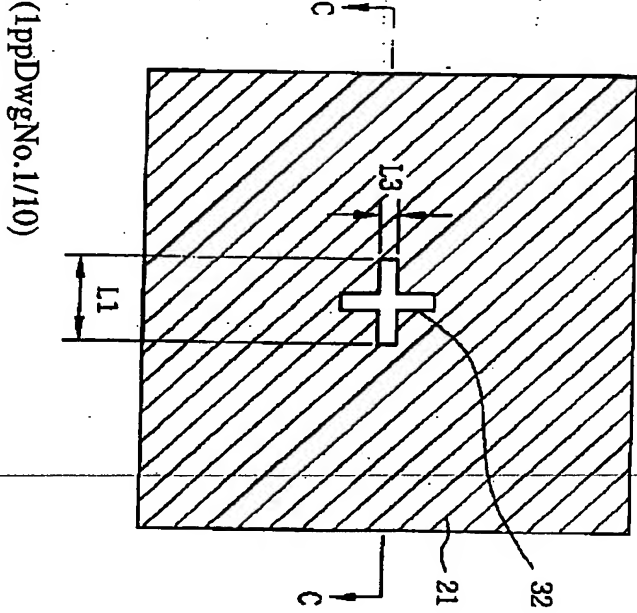


<p>2002-358942/39 L03 SMSU 2000.05.26 SAMSUNG ELECTRONICS CO LTD *KR 2001107242-A 2000.05.26 2000-028589(+2000KR-028589) (2001.12.07) H01L 21/027 Phase shift mask C2002-101854 Addtl. Data: SON C J</p>	<p>L(4-C6A, 4-C10F)</p>
<p><u>NOVELTY</u> A phase shift mask is provided to enhance an integration rate of a semiconductor device by forming stably a margin of a photo process for forming a contact hole of a fine pattern.</p> <p><u>DETAILED DESCRIPTION</u> A phase shift layer(21) is stacked on a whole face of a permeable quartz substrate. An aperture(32) of a cross shape is formed on a center portion of the phase shift layer(21). The aperture(32) is used for forming a contact hole. A width(L3) and a length(L1) of the aperture(32) can be optimized according to a size of the contact hole. A molybdenum silicide layer having transmissivity of 8 percent can be used as the phase shift layer(21). In order to improve a resolution, the transmissivity of the phase shift layer(21) is controlled according to a thickness of the phase shift layer(21).</p>	 <p>(1ppDwgNo.1/10)</p> <p>KR 2001107242-A</p>